

ISC Silicon NPN Power Transistor

2SC3569

DESCRIPTION

- · Low Collector Saturation Voltage
- · High switching speed
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

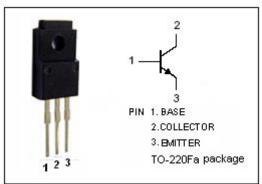


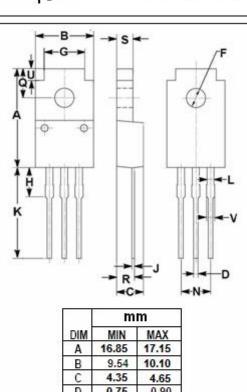
APPLICATIONS

 Especially suited for high voltage, high speed and high power switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|---------|------------|
| V _{CBO} | Collector-Base Voltage | 500 | V |
| V _{CEO} | Collector-Emitter Voltage | 400 | V |
| V _{EBO} | Emitter-Base Voltage | 7 | V |
| Ic | Collector Current-Continuous | 2 | А |
| Ісм | Collector Current-Pulse | 4 | Α |
| I _B | Base Current-Continuous | 0.5 | А |
| Pc | Collector Power Dissipation @ T _C =25 °C | 15 | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range | -55~150 | $^{\circ}$ |





| - 1 | 1111111 | |
|-----|---------|-------|
| DIM | MIN | MAX |
| Α | 16.85 | 17.15 |
| В | 9.54 | 10.10 |
| C | 4.35 | 4.65 |
| D | 0.75 | 0.90 |
| F | 3.20 | 3.40 |
| G | 6.90 | 7.20 |
| Н | 5.15 | 5.45 |
| J | 0.45 | 0.75 |
| K | 13.35 | 13.65 |
| L | 1.10 | 1.30 |
| N | 4.98 | 5.18 |
| Q | 4.85 | 5.15 |
| R | 2.55 | 3.25 |
| S | 2.70 | 2.90 |
| U | 1.75 | 2.05 |
| V | 1.30 | 1.50 |



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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | I _C = 10mA ; I _B = 0 | 400 | | | V |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 0.7A; I _B = 0.14A | | | 1.0 | V |
| V _{BE(sat)} | Base-Emitter Saturation Voltage | I _C = 0.7A; I _B = 0.14A | | | 1.2 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 500V; I _E = 0 | | | 100 | μА |
| I _{EBO} | Emitter Cutoff Current | V _{EB} =7V; I _C = 0 | | | 100 | μА |
| h _{FE-1} | DC Current Gain | I _C = 0.2A; V _{CE} = 5V | 20 | | 80 | |
| h _{FE-2} | DC Current Gain | I _C = 0.5A ; V _{CE} = 5V | 10 | | | |

♦ h_{FE} Classifications

| м | L | к | |
|-------|-------|-------|---|
| 20-40 | 30-60 | 40-80 |) |

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